

50 A VRPower® Integrated Power Stage

DESCRIPTION

The SiC653A is an integrated power stage solution optimized for synchronous buck applications to offer high current, high efficiency, and high power density performance. Packaged in Vishay's 5 mm x 5 mm MLP package, SiC653A enables voltage regulator designs to deliver up to 50 A continuous current per phase.

The internal power MOSFETs utilizes Vishay's state-of-the-art Gen IV TrenchFET technology that delivers industry benchmark performance to significantly reduce switching and conduction losses.

The SiC653A incorporates an advanced MOSFET gate driver IC that features high current driving capability, adaptive dead-time control, an integrated bootstrap Schottky diode, a thermal warning (THWn) that alerts the system of excessive junction temperature, and zero current detect to improve light load efficiency. The drivers are also compatible with a wide range of PWM controllers and supports tri-state PWM, 3.3 V and 5 V logic.

FEATURES

- Thermally enhanced PowerPAK® MLP55-31L package
- Vishay's Gen V MOSFET technology and a low-side MOSFET with integrated Schottky diode
- Delivers in excess of 50 A continuous current, 70 A peak (10 ms) and 100 A peak (10 μ s)
- 95 % peak efficiency
- High frequency operation up to 1.5 MHz
- Power MOSFETs optimized for 12 V input stage
- 3.3 V and 5 V PWM logic with tri-state and hold-off
- Zero current detect control for light load efficiency improvement
- Low PWM propagation delay (< 20 ns)
- Thermal monitor flag
- Under voltage lockout protection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Multi-phase VRDs for CPU, GPU, and memory

TYPICAL APPLICATION DIAGRAM

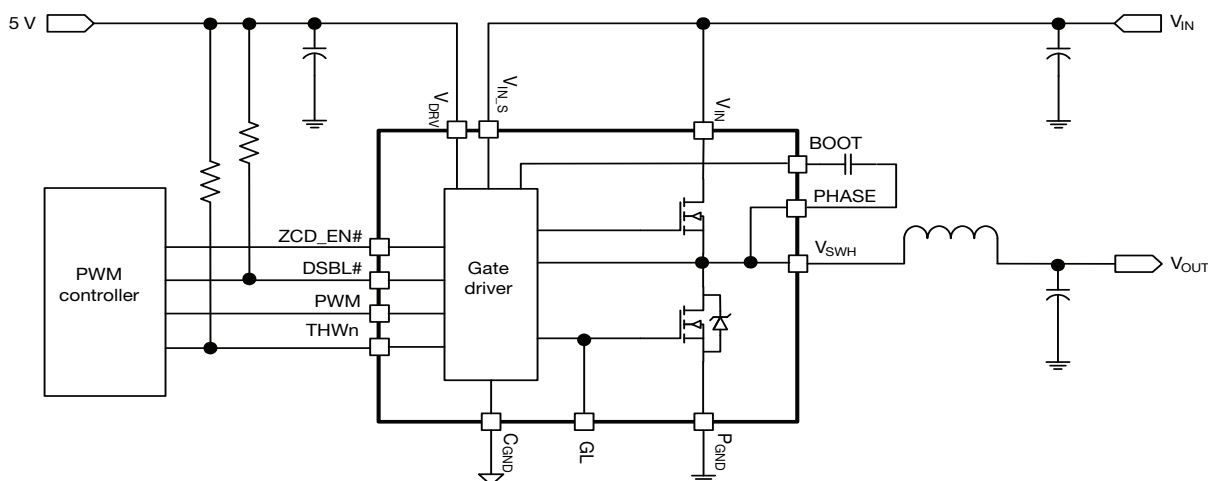
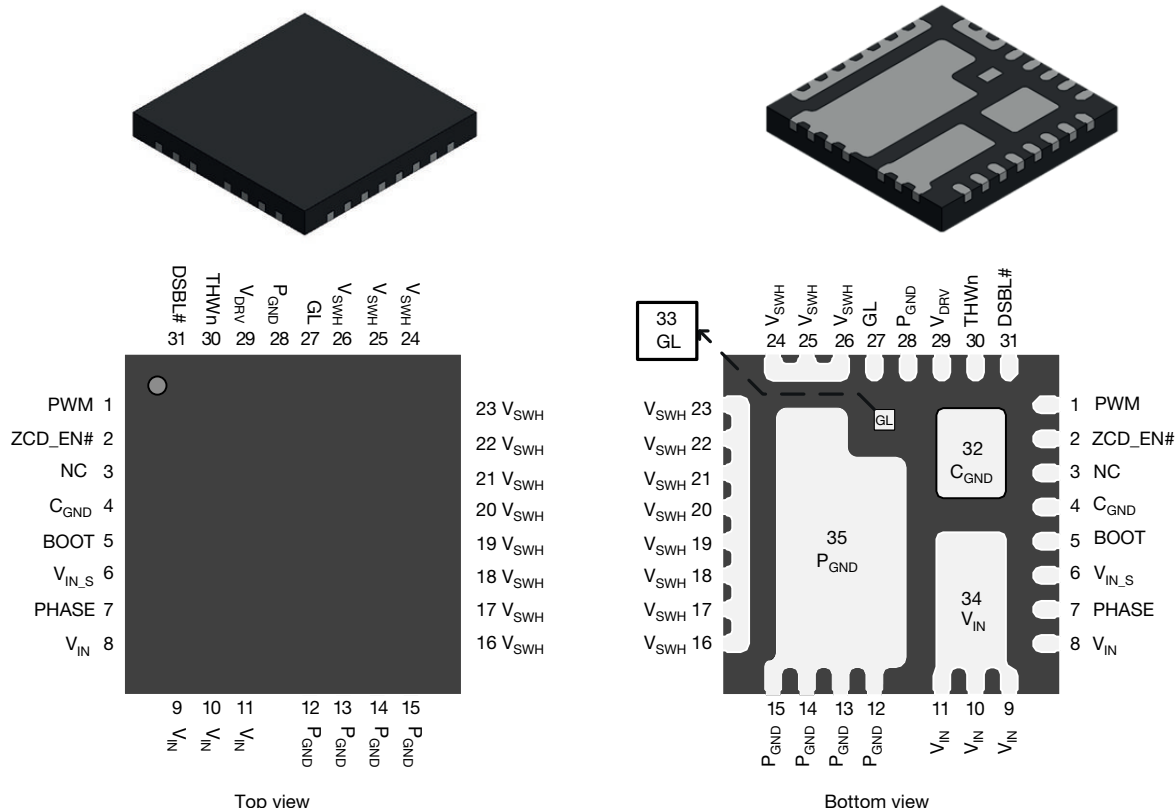


Fig. 1 - SiC653A Typical Application Diagram

PINOUT CONFIGURATION

Fig. 2 - SiC653A Pin Configuration

PIN CONFIGURATION		
PIN NUMBER	NAME	FUNCTION
1	PWM	PWM control input
2	ZCD_EN#	Internal connect to V_{CC} through a 40 k Ω resistor. CCM is active when floating the pin. Connect the pin to GND enable the diode emulation mode
3	NC	Not internally connected
4, 32	C _{GND}	Analog ground for the driver IC
5	BOOT	High-side driver bootstrap voltage
6	V _{IN,S}	Over current protection input voltage, connect this pin to power stage input voltage
7	PHASE	Return path of high-side gate driver
8 to 11, 34	V _{IN}	Power stage input voltage. Drain of high-side MOSFET
12 to 15, 28, 35	P _{GND}	Power ground
16 to 26	V _{SWH}	Switch node of the power stage
27, 33	GL	Low-side gate signal
29	V _{DRV}	Supply voltage for internal gate driver
30	THWn	Thermal warning open drain output
31	DSBL#	Disable pin. Active low

ORDERING INFORMATION			
PART NUMBER	PACKAGE	MARKING CODE	OPTION
SiC653ACD-T1-GE3	PowerPAK MLP55-31L	SiC653A	3.3 V PWM optimized
SiC653ADB	Reference board		



ABSOLUTE MAXIMUM RATINGS			
ELECTRICAL PARAMETER	SYMBOL	LIMIT	UNIT
Input voltage	V_{IN}	-0.3 to +30	V
Drive supply voltage	V_{DRV}	-0.3 to +7	
Switching / phase node (DC)	V_{SW} / V_{PH}	-0.3 to +30	
Switching / phase node (AC) ⁽¹⁾		-14 to +35	
Input to phase (DC)	$V_{IN-PHASE}$	-0.3 to +30	
Input to phase (AC) ⁽¹⁾		-14 to +35	
BOOT voltage (DC)	V_{BOOT}	-0.3 to +37	
BOOT voltage (AC) ⁽²⁾		-7 to +40	
BOOT to switching / phase (DC)	$V_{BOOT-PHASE}$	-0.3 to +7	
BOOT to switching / phase (AC) ⁽²⁾		-0.3 to +9	
All logic inputs and outputs (PWM, DSBL#, and THWn)		-0.3 to $V_{DRV} + 0.3$	
Max. operating junction temperature	T_J	150	°C
Ambient temperature	T_A	-40 to +125	
Storage temperature	T_{stg}	-65 to +150	
Electrostatic discharge protection	Human body model, JESD22-A114	3000	V
	Charged device model, JESD22-C101	1000	

Notes

- Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability
- ⁽¹⁾ The specification values indicated “AC” is V_{SW} / V_{PH} to P_{GND} , or V_{IN} to V_{PHASE} , at -14 V (< 10 ns, 10 μ J), min. and 35 V (< 50 ns), max.
- ⁽²⁾ The specification value indicates “AC voltage” is V_{BOOT} to P_{GND} , -7 V (< 20ns) min and 40V (< 50ns) max., or V_{BOOT} to $V_{SW/PHASE}$, -0.3 V min. and 9 V (< 20ns) max.

RECOMMENDED OPERATING RANGE				
ELECTRICAL PARAMETER	MINIMUM	TYPICAL	MAXIMUM	UNIT
Input voltage (V_{IN})	4.5	-	24	V
Drive supply voltage (V_{DRV})	4.5	5	5.5	
BOOT to PHASE ($V_{BOOT-PHASE}$, DC voltage)	4	4.5	5.5	
Thermal resistance from junction to ambient	-	10.6	-	°C/W
Thermal resistance from junction to case	-	1.6	-	

**ELECTRICAL SPECIFICATIONS**(DSBL# = ZCD_EN# = 5 V, V_{IN} = 12 V, V_{DRV} = 5 V, T_A = 25 °C)

PARAMETER	SYMBOL	TEST CONDITION	LIMITS			UNIT
			MIN.	TYP.	MAX.	
POWER SUPPLY						
Drive supply current	I _{VDRV}	f _S = 300 kHz, D = 0.1	-	15	25	mA
		f _S = 1 MHz, D = 0.1	-	50	-	
		V _{DSBL#} = 0 V, no switching	-	25	-	μA
		V _{DSBL#} = 5 V, no switching	-	60	-	
BOOTSTRAP SUPPLY						
Bootstrap diode forward voltage	V _F	I _F = 2 mA	-	-	0.4	V
PWM CONTROL INPUT						
Rising threshold	V _{TH_PWM_R}	V _{PWM} = FLOAT	2.2	2.45	2.7	V
Falling threshold	V _{TH_PWM_F}		0.72	0.9	1.1	
Tri-state voltage	V _{TRI}		-	1.8	-	
Tri-state rising threshold	V _{TRI_TH_R}		0.9	1.15	1.38	
Tri-state falling threshold	V _{TRI_TH_F}		1.95	2.2	2.45	
Tri-state rising threshold hysteresis	V _{HYS_TRI_R}	-	250	-	mV	
Tri-state falling threshold hysteresis	V _{HYS_TRI_F}	-	300	-		
PWM input current	I _{PWM}	V _{PWM} = 3.3 V	-	-	225	μA
		V _{PWM} = 0 V	-	-	-225	
TIMING SPECIFICATIONS						
Tri-state to GH/GL rising propagation delay	t _{PD_TRI_R}	No load, see fig. 4	-	30	-	ns
Tri-state hold-off time	t _{TSHO}		-	130	-	
GH - turn off propagation delay	t _{PD_OFF_GH}		-	15	-	
GH - turn on propagation delay (dead time rising)	t _{PD_ON_GH}		-	10	-	
GL - turn off propagation delay	t _{PD_OFF_GL}		-	12	-	
GL - turn on propagation delay (dead time falling)	t _{PD_ON_GL}		-	10	-	
DSBL# Lo to GH/GL falling propagation delay	t _{PD_DSBL#_F}	Fig. 5	-	15	-	
PWM minimum on-time	t _{PWM_ON_MIN}		30	-	-	

**ELECTRICAL SPECIFICATIONS**(DSBL# = ZCD_EN# = 5 V, V_{IN} = 12 V, V_{DRV} = 5 V, T_A = 25 °C)

PARAMETER	SYMBOL	TEST CONDITION	LIMITS			UNIT
			MIN.	TYP.	MAX.	
DSBL# INPUT						
DSBL# logic input voltage	V _{IH_DSBL#}	Input logic high	2	-	-	V
	V _{IL_DSBL#}	Input logic low	-	-	0.8	
PROTECTION						
Under voltage lockout	V _{UVLO}	V _{DRV} rising, on threshold	-	3.7	4.1	V
		V _{DRV} falling, off threshold	2.7	3.1	-	
Under voltage lockout hysteresis	V _{UVLO_HYST}		-	575	-	mV
THWn flag set ⁽²⁾	T _{THWn_SET}		-	160	-	°C
THWn flag clear ⁽²⁾	T _{THWn_CLEAR}		-	135	-	
THWn flag hysteresis ⁽²⁾	T _{THWn_HYST}		-	25	-	
THWn output low	V _{OL_THWn}	I _{THWn} = 2 mA	-	0.02	-	V

Notes

(1) Typical limits are established by characterization and are not production tested

(2) Guaranteed by design

DETAILED OPERATIONAL DESCRIPTION**PWM Input with Tri-state Function**

The PWM input receives the PWM control signal from the VR controller IC. The PWM input is designed to be compatible with standard controllers using two state logic (H and L) and advanced controllers that incorporate tri-state logic (H, L and tri-state) on the PWM output. For two state logic, the PWM input operates as follows. When PWM is driven above $V_{PWM_TH_R}$ the low-side is turned on and the high-side is turned on. When PWM input is driven below $V_{PWM_TH_F}$ the high-side is turned OFF and the low-side is turned ON. For tri-state logic, the PWM input operates as previously stated for driving the MOSFETs. However, there is a third state that is entered as the PWM output of tri-state compatible controller enters its high impedance state during shut-down. The high impedance state of the controller's PWM output allows the SiC653A to pull the PWM input into the tri-state region (see PWM Timing Diagram). If the PWM input stays in this region for the tri-state hold-off period, t_{TSHO} , both high-side and low-side MOSFETs are turned OFF. This function allows the VR phase to be disabled without negative output voltage swing caused by inductor ringing and saves a Schottky diode clamp. The PWM and tri-state regions are separated by hysteresis to prevent false triggering. The SiC653A incorporates PWM voltage thresholds that are compatible with 3.3 V logic and the SiC653A thresholds are compatible with 5 V logic.

Disable (DSBL#)

In the low state, the DSBL# pin shuts down the driver IC and disables both high-side and low-side MOSFETs. In this state, standby current is minimized. If DSBL# is left unconnected, an internal pull-down resistor will pull the pin to C_{GND} and shut down the IC.

Thermal Shutdown Warning (THWn)

The THWn pin is an open drain signal that flags the presence of excessive junction temperature. Connect with a maximum of 20 k Ω , to V_{DRV} . An internal temperature sensor detects the junction temperature. The temperature threshold is 160 °C. When this junction temperature is exceeded the THWn flag is set. When the junction temperature drops below 135 °C the device will clear the THWn signal. The SiC653A does not stop operation when the flag is set. The decision to shutdown must be made by an external thermal control function.

Voltage Input (V_{IN})

This is the power input to the drain of the high-side power MOSFET. This pin is connected to the high power intermediate BUS rail.

Switch Node (V_{SWH} and PHASE)

The switch node, V_{SWH} , is the circuit power stage output. This is the output applied to the power inductor and output filter to deliver the output for the buck converter. The PHASE pin is internally connected to the switch node V_{SWH} . This pin is to be used exclusively as the return pin for the BOOT capacitor. A 20 k Ω resistor is connected between GH and PHASE to provide a discharge path for the HS MOSFET in the event that V_{DRV} goes to zero while V_{IN} is still applied.

Ground Connections (C_{GND} and P_{GND})

P_{GND} (power ground) should be externally connected to C_{GND} (control signal ground). The layout of the printed circuit board should be such that the inductance separating C_{GND} and P_{GND} is minimized. Transient differences due to inductance effects between these two pins should not exceed 0.5 V

Control and Drive Supply Voltage Input (V_{DRV})

V_{DRV} is the bias supply for the gate drivers and the gate drive control IC. It is recommended to connect a 2.2 μF decoupling capacitor from this pin to GND. This creates a low pass filtering effect to avoid coupling of high frequency gate drive noise into the IC.

Bootstrap Circuit (BOOT)

The internal bootstrap diode and an external bootstrap capacitor form a charge pump that supplies voltage to the BOOT pin. An integrated bootstrap diode is incorporated so that only an external capacitor is necessary to complete the bootstrap circuit. Connect a boot strap capacitor with one leg tied to BOOT pin and the other tied to PHASE pin.

Shoot-Through Protection and Adaptive Dead Time

The SiC653A has an internal adaptive logic to avoid shoot through and optimize dead time. The shoot through protection ensures that both high-side and low-side MOSFETs are not turned ON at the same time. The adaptive dead time control operates as follows. The HS and LS gate voltages are monitored to prevent the one turning ON from tuning ON until the other ($< 1\text{ V}$). Built in delays also ensure that one power MOS is completely OFF, before the other can be turned ON. This feature helps to adjust dead time as gate transitions change with respect to output current and temperature. Change with respect to output current and temperature.

Under Voltage Lockout (UVLO)

During the start up cycle, the UVLO disables the gate drive holding high-side and low-side MOSFET gates low until the supply voltage rail has reached a point at which the logic circuitry can be safely activated. The SiC653A also incorporates logic to clamp the gate drive signals to zero when the UVLO falling edge triggers the shutdown of the device. As an added precaution, a 20 $\text{k}\Omega$ resistor is connected between GH and PHASE to provide a discharge path for the HS MOSFET.

Diode Emulation Mode (ZCD_EN#)

The ZCD_EN# pin enables or disables diode emulation mode. When ZCD_EN# is driven below $V_{TH_ZCD_EN\#_F}$, diode emulation is allowed. When ZCD_EN# is driven above $V_{TH_ZCD_EN\#_R}$, continuous conduction mode is forced. Diode emulation mode allows for higher converter efficiency under light load situations. With diode emulation active, the SiC653A will detect the zero current crossing of the output inductor and turn off the low side MOSFET. This ensures that discontinuous conduction mode (DCM) is achieved. Diode emulation is asynchronous to the PWM signal, therefore, the SiC653A will respond to the ZCD_EN# input immediately after it changes state.

FUNCTIONAL BLOCK DIAGRAM

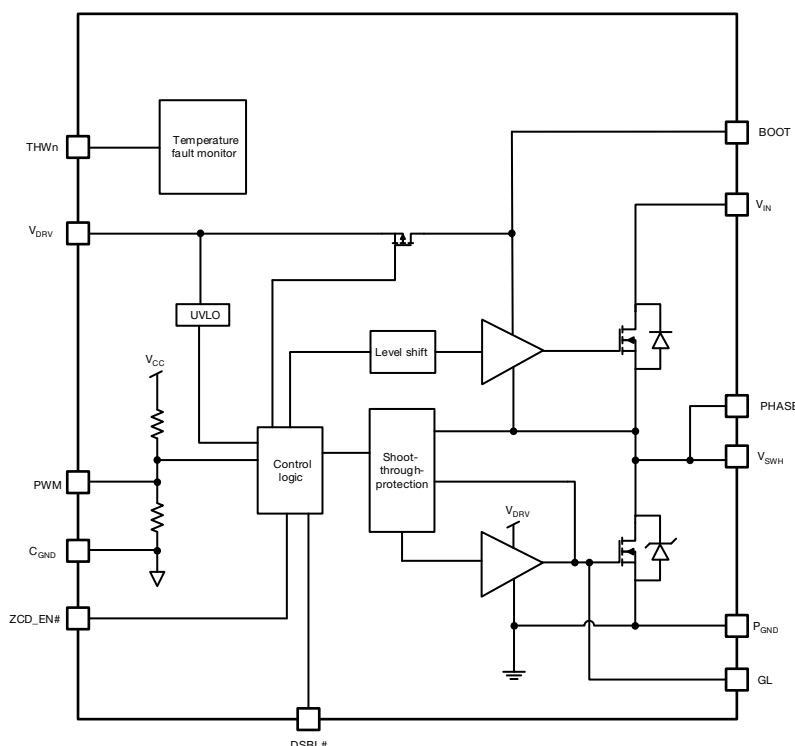


Fig. 3 - SiC653A Functional Block Diagram

DEVICE TRUTH TABLE				
DSBL#	ZCD_EN#	PWM	GH	GL
L	X	X	L	L
H	L	L	L	$H, I_L > 0\text{ A}$ $L, I_L < 0\text{ A}$
H	L	H	H	L
H	L	Tri-state	L	L
H	H, default	L	L	H
H	H, default	H	H	L
H	H, default	Tri-state	L	L

PWM TIMING DIAGRAM

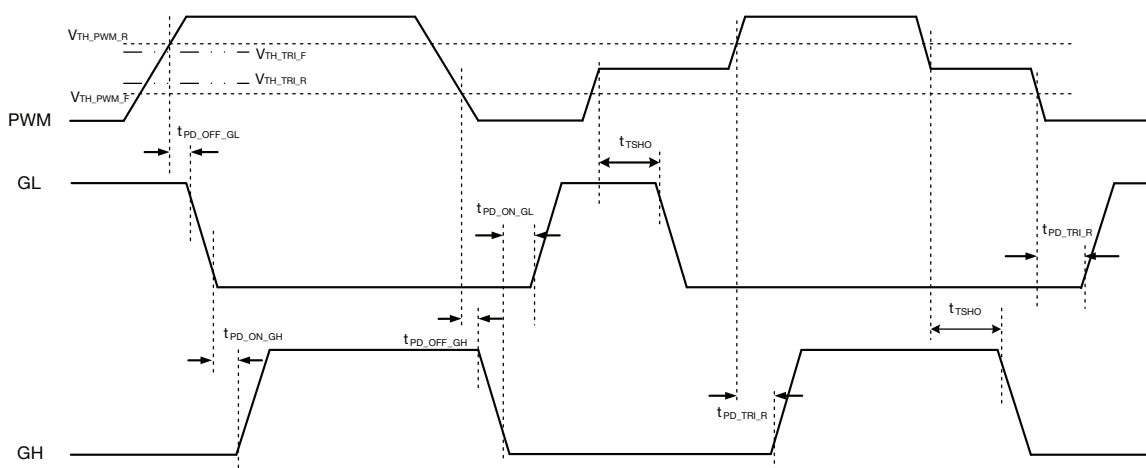


Fig. 4 - Definition of PWM Logic and Tri-state

DSBL# PROPAGATION DELAY

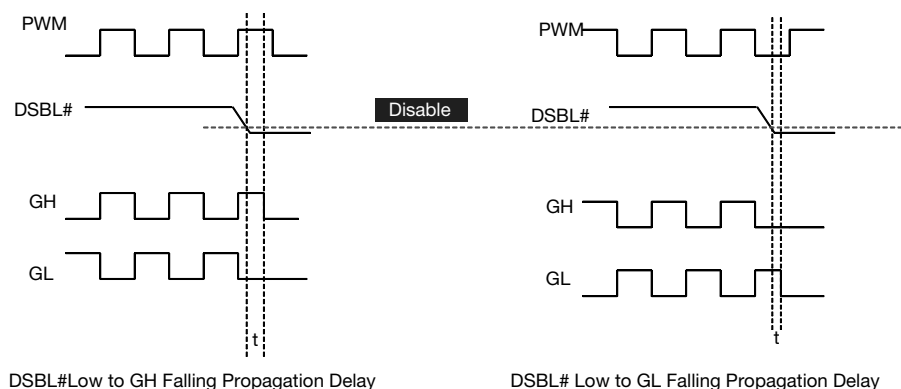


Fig. 5 - DSBL# Falling Propagation Delay

ELECTRICAL CHARACTERISTICS

Test condition: $V_{IN} = 12\text{ V}$, $V_{DRV} = 5\text{ V}$, $ZCD_EN\# = 5\text{ V}$, $V_{OUT} = 1.8\text{ V}$, $L_{OUT} = 250\text{ nH}$ ($DCR = 0.32\text{ m}\Omega$), $T_A = 25\text{ }^\circ\text{C}$, natural convection cooling
(All power loss and normalized power loss curves show SiC653A losses only unless otherwise stated)

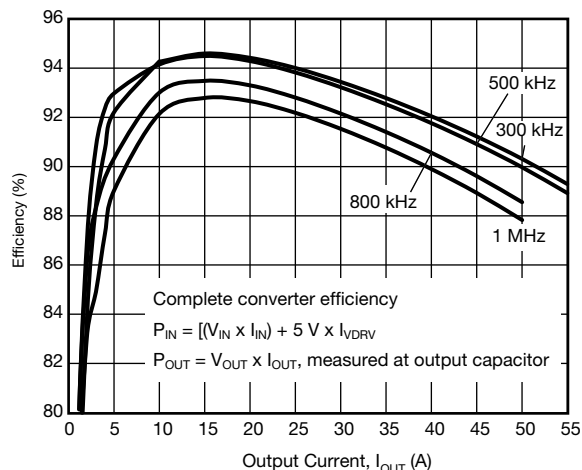


Fig. 6 - Efficiency vs. Output Current

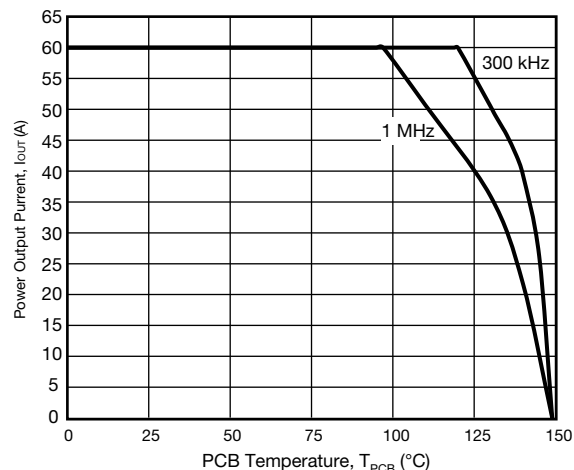


Fig. 9 - Safe Operating Area

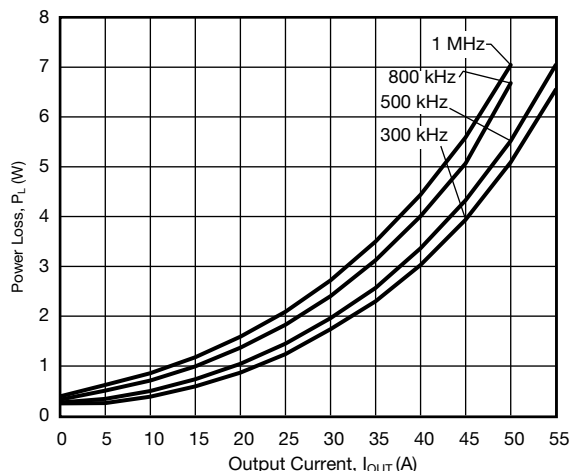


Fig. 7 - Power Loss vs. Output Current

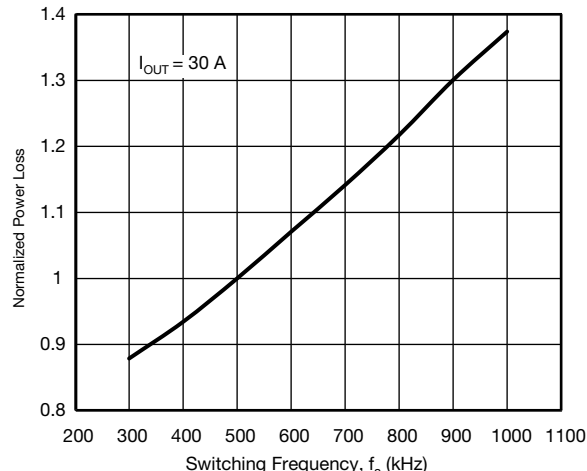


Fig. 10 - Power Loss vs. Switching Frequency

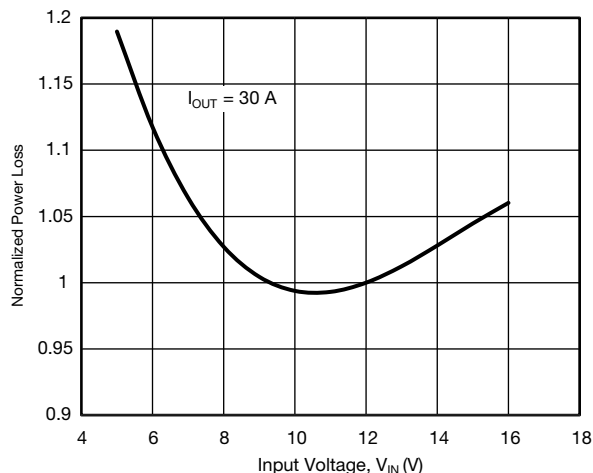


Fig. 8 - Power Loss vs. Input Voltage

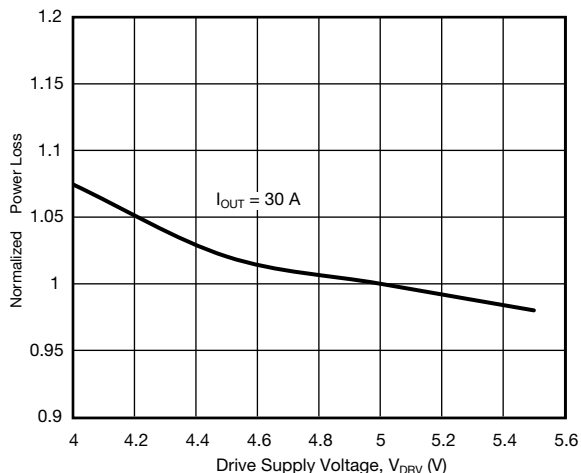


Fig. 11 - Power Loss vs. Drive Supply Voltage

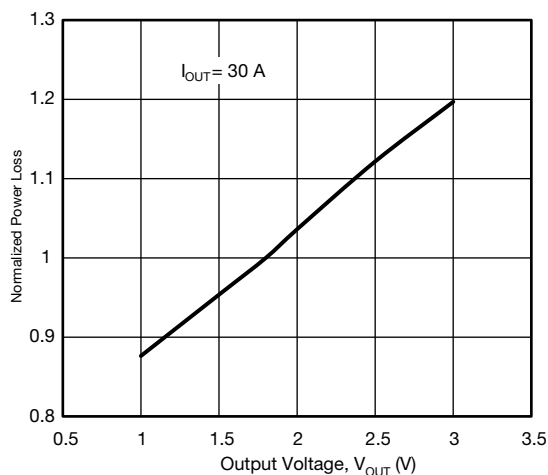


Fig. 12 - Power Loss vs. Output Voltage

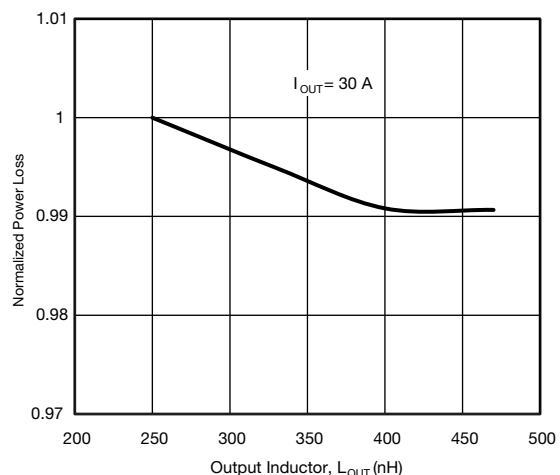


Fig. 15 - Power Loss vs. Output Inductor

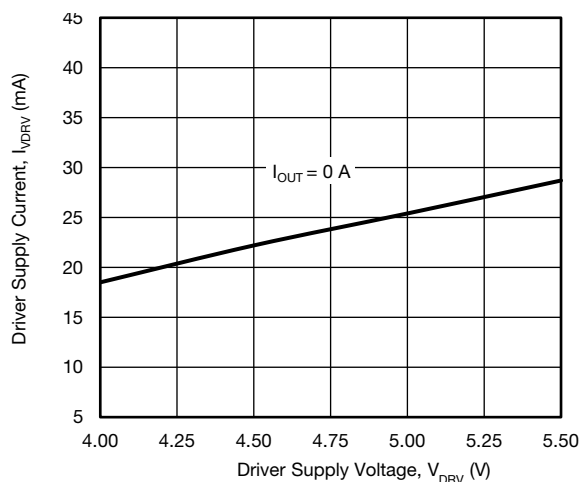


Fig. 13 - Driver Supply Current vs. Driver Supply Voltage

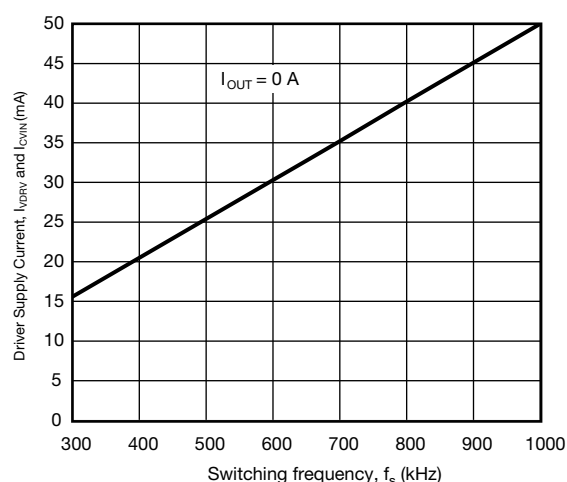


Fig. 16 - Driver Supply Current vs. Switching Frequency

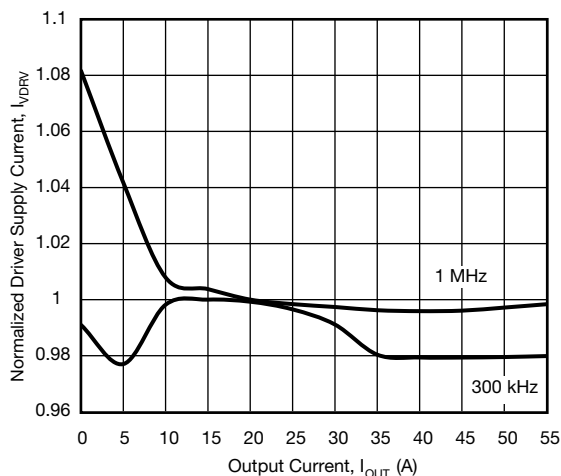


Fig. 14 - Driver Supply Current vs. Output Current

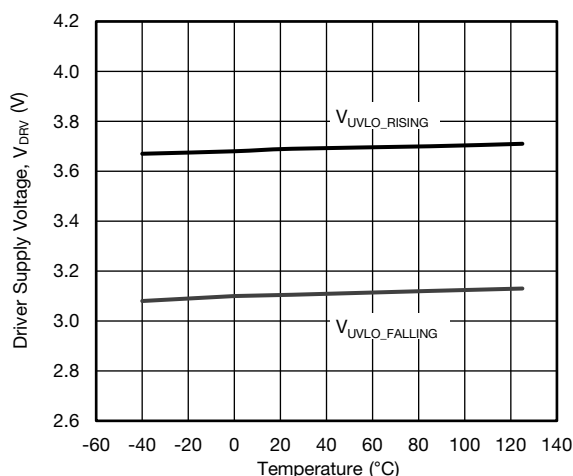


Fig. 17 - UVLO Threshold vs. Temperature

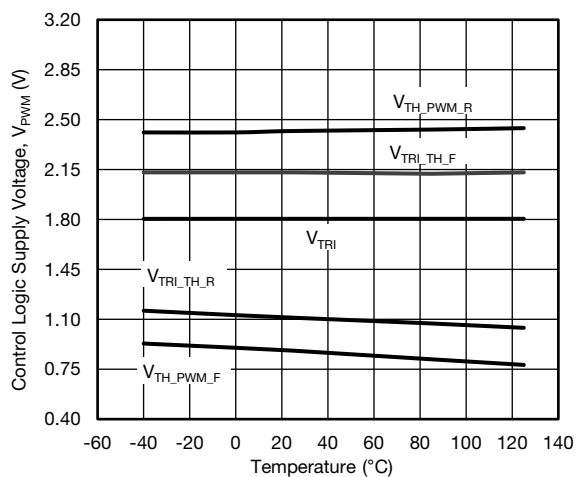


Fig. 18 - PWM Threshold vs. Temperature (SiC653A)

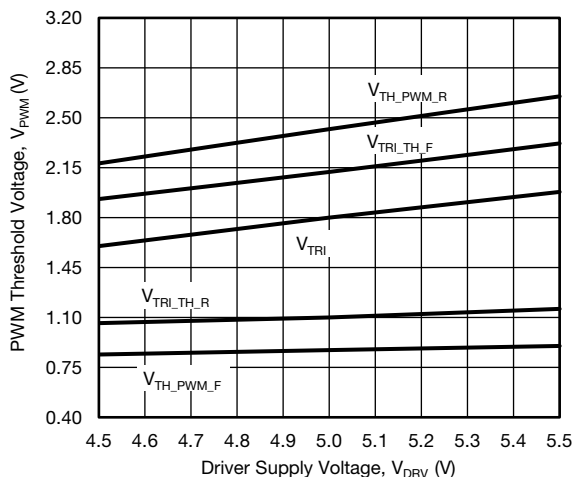


Fig. 21 - PWM Threshold vs. Driver Supply Voltage (SiC653A)

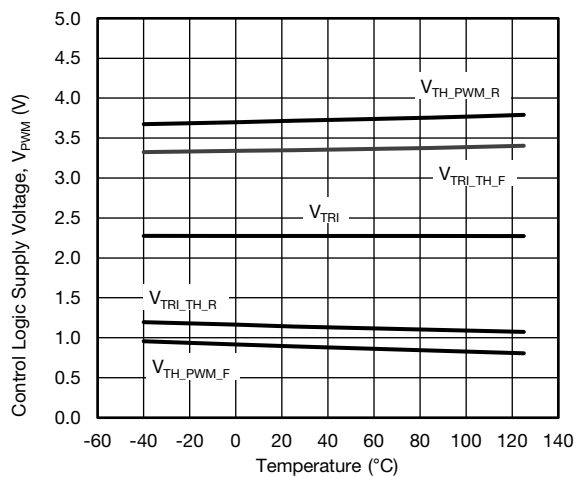


Fig. 19 - PWM Threshold vs. Temperature (SiC653)

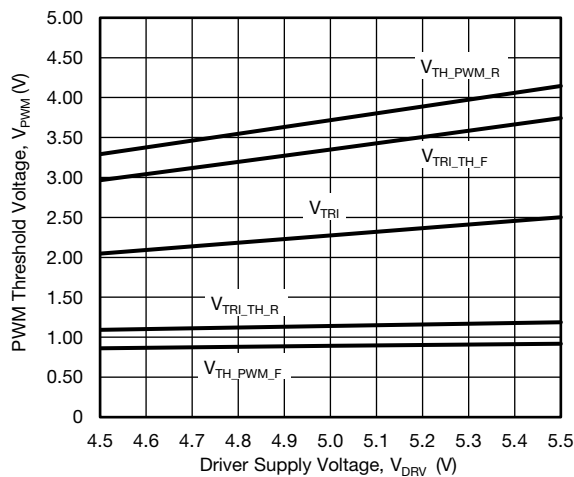


Fig. 22 - PWM Threshold vs. Driver Supply Voltage (SiC653)

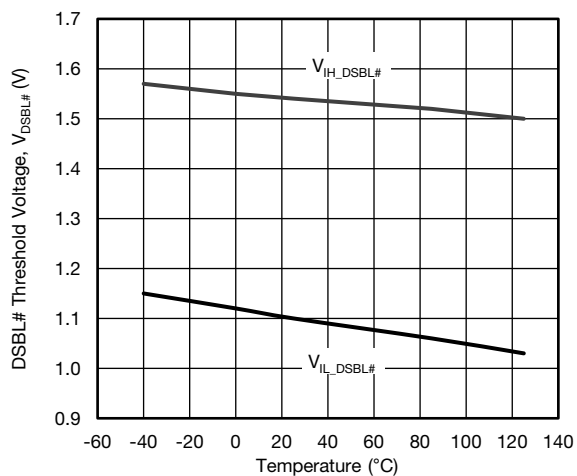


Fig. 20 - DSBL# Threshold vs. Temperature

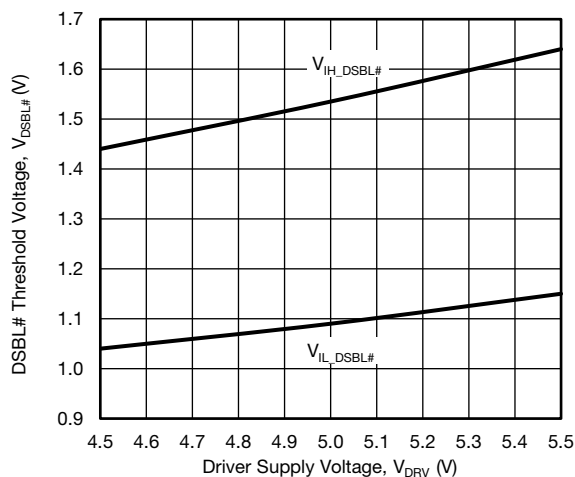


Fig. 23 - DSBL# vs. Driver Input Voltage

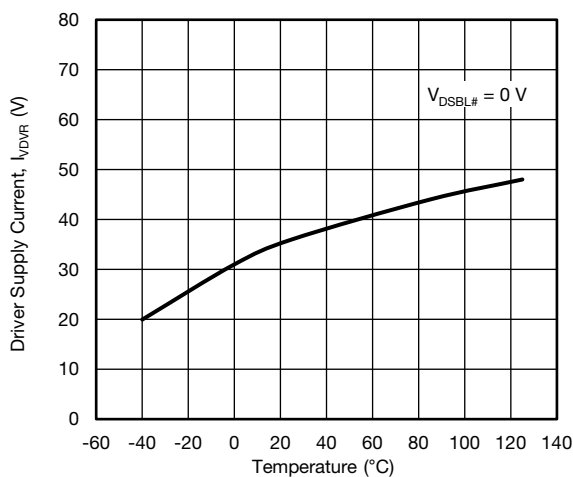


Fig. 26 - Driver Shutdown Current vs. Temperature

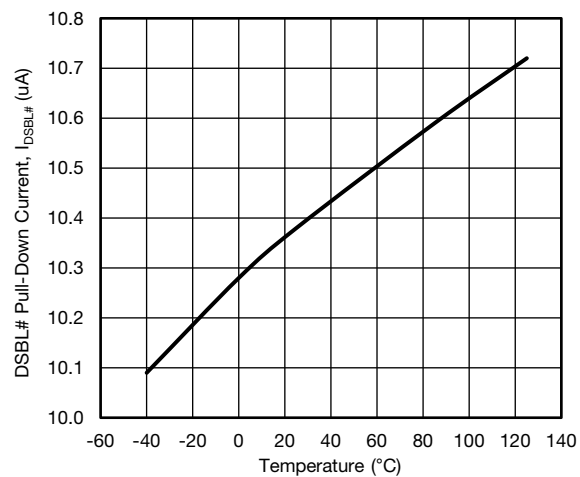


Fig. 24 - DSBL# Pull-Down Current vs. Temperature

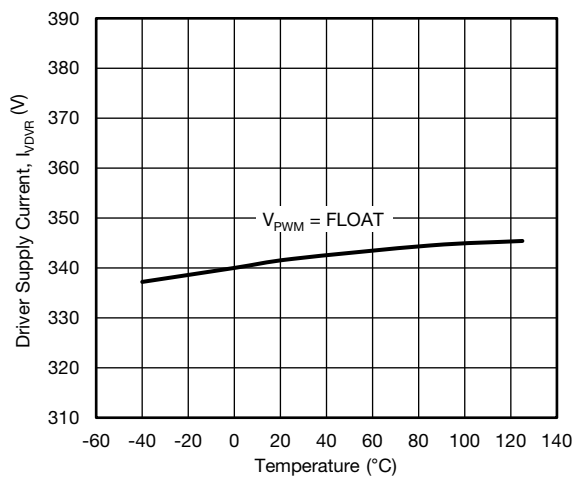


Fig. 27 - Driver Supply Current vs. Temperature

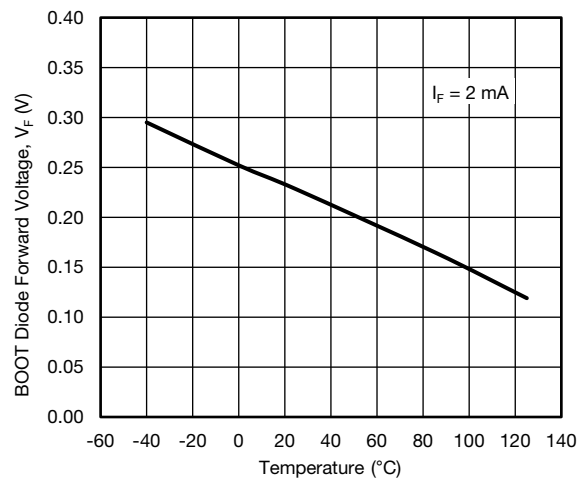
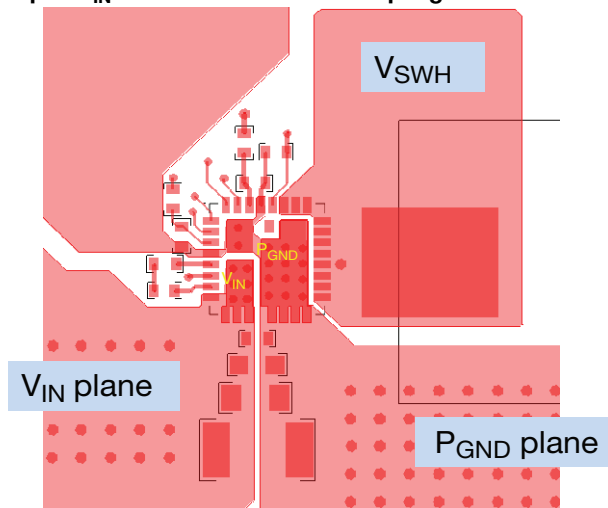


Fig. 25 - Boot Diode Forward Voltage vs. Temperature

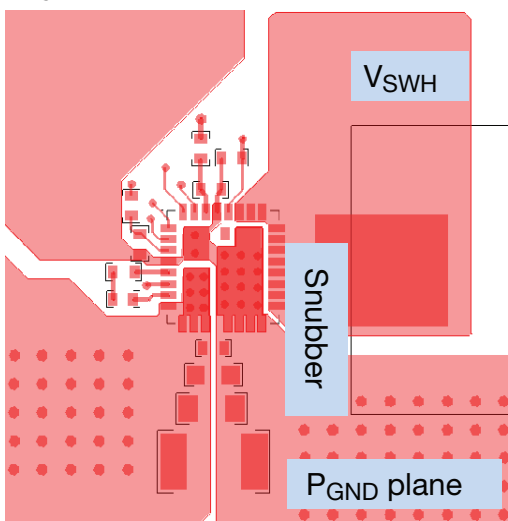
PCB LAYOUT RECOMMENDATIONS

Step 1: V_{IN} /GND Planes and Decoupling



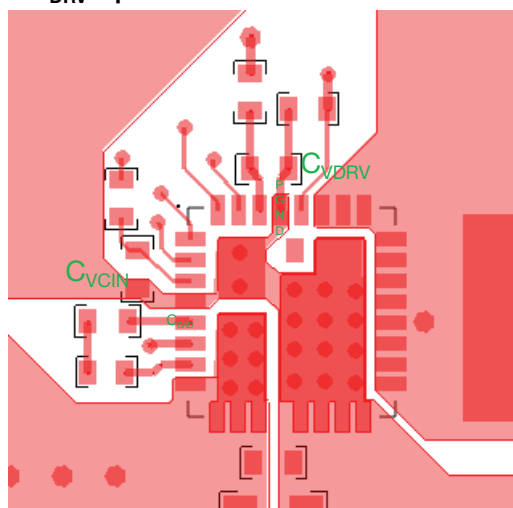
1. Layout V_{IN} and P_{GND} planes as shown above
2. Ceramic capacitors should be placed right between V_{IN} and P_{GND} , and very close to the device for best decoupling effect
3. Difference values / packages of ceramic capacitors should be used to cover entire decoupling spectrum e.g. 1210, 0805, 0603 and 0402
4. Smaller capacitance value, closer to device V_{IN} pin(s) - better high frequency noise absorbing

Step 2: V_{SWH} Plane



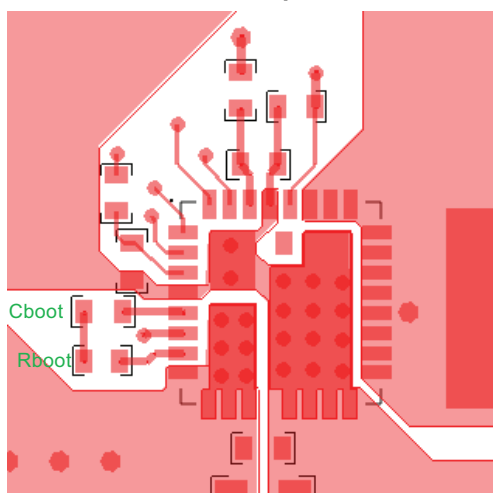
1. Connect output inductor to DrMOS with large plane to lower the resistance
2. If any snubber network is required, place the components as shown above and the network can be placed at bottom

Step 3: V_{DRV} Input Filter



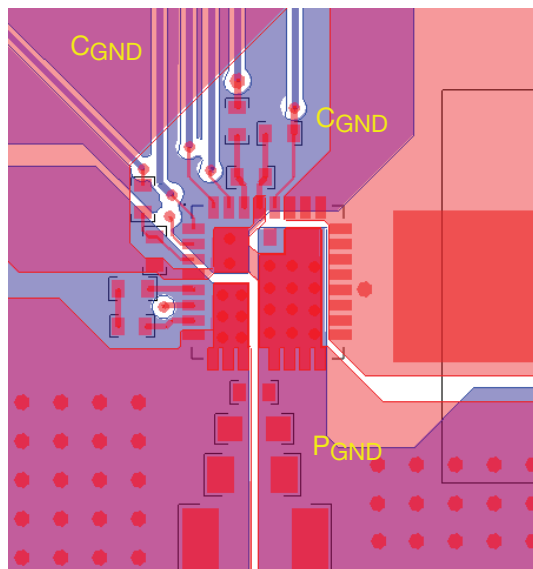
3. The V_{DRV} input filter ceramic cap should be placed very close to IC. It is recommended to connect two caps separately.
4. C_{VDRV} cap should be placed between pin 28 (P_{GND} of driver IC) and pin 29 to provide maximum instantaneous driver current for low-side MOSFET during switching cycle
5. For connecting C_{VDRV} analog ground, it is recommended to use large plane to reduce parasitic inductance.

Step 4: BOOT Resistor and Capacitor Placement



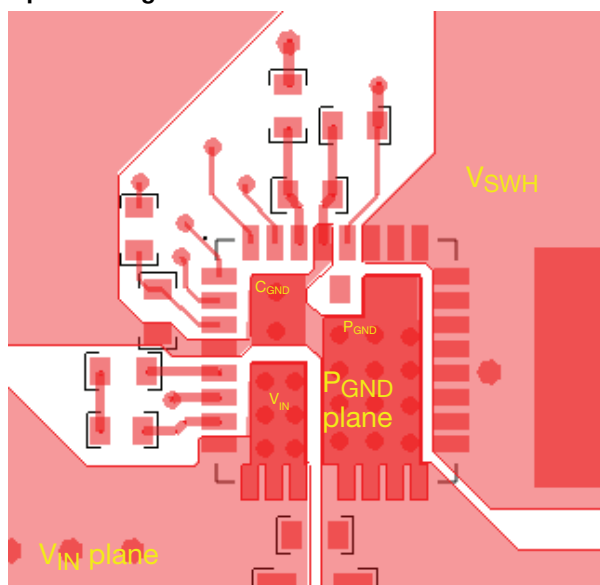
1. These components need to be placed very close to IC, right between PHASE (pin 7) and BOOT (pin 5).
2. To reduce parasitic inductance, chip size 0402 can be used.

Step 5: Signal Routing



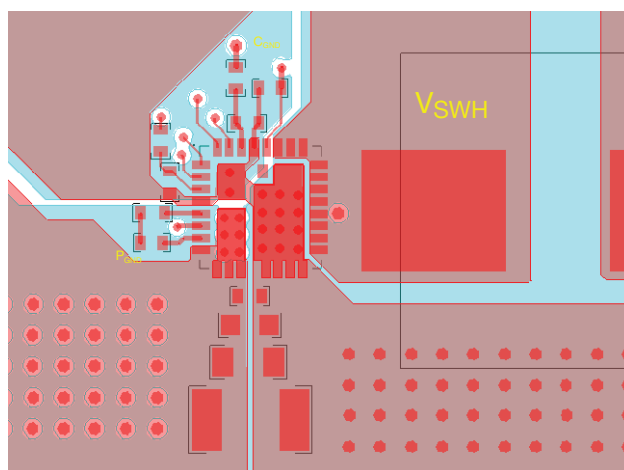
1. Route the PWM / ZCD_EN# / DSBL# / THWn signal traces out of the top left corner next DrMOS pin 1.
2. PWM signal is very important signal, both signal and return traces need to pay special attention of not letting this trace cross any power nodes on any layer.
3. It is best to “shield” traces from power switching nodes, e.g. V_{SWH}, to improve signal integrity.
4. GL (pin 27) has been connected with GL pad internally and does not need to connect externally.

Step 6: Adding Thermal Relief Vias



5. Thermal relief vias can be added on the V_{IN} and P_{GND} pads to utilize inner layers for high-current and thermal dissipation.
6. To achieve better thermal performance, additional vias can be put on V_{IN} plane and P_{GND} plane.
7. V_{SWH} pad is a noise source and not recommended to put vias on this plane.
8. 8 mil drill for pads and 10 mils drill for plane can be the optional via size. Vias on pad may drain solder during assembly and cause assembly issue. Please consult with the assembly house for guideline.

Step 7: Ground Connection



9. It is recommended to make single connection between C_{GND} and P_{GND} and this connection can be done on top layer.
10. It is recommended to make the whole inner 1 layer (next to top layer) ground plane and separate them into C_{GND} and P_{GND} plane.
11. These ground planes provide shielding between noise source on top layer and signal trace on bottom layer.

Multi-Phases VRPower PCB Layout

Following is an example for 6 phase layout. As can be seen, all the VRPower stages are lined in X-direction compactly with decoupling caps next to them. The inductors are placed as close as possible to the SiC653A to minimize the PCB copper loss. Vias are applied on all PADs (V_{IN} , P_{GND} , C_{GND}) of the SiC653A to ensure that both electrical and thermal performance are excellent. Large copper planes are used for all the high current loops, such as V_{IN} , V_{SWH} , V_{OUT} and P_{GND} . These copper planes are duplicated in other layers to minimize the inductance and resistance. All the control signals are routed from the SiC653A to a controller placed to the north of the power stage through inner layers to avoid the overlap of high current loops. This achieves a compact design with the output from the inductors feeding a load located to the south of the design as shown in the figure.

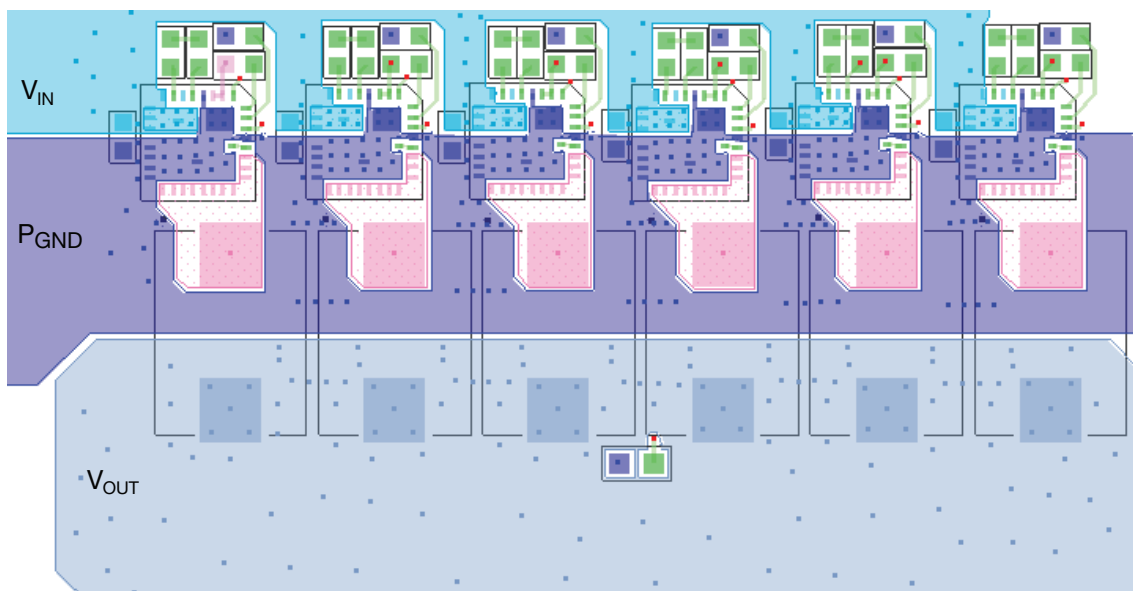


Fig. 28 - Multi - Phase VRPower Layout Top View

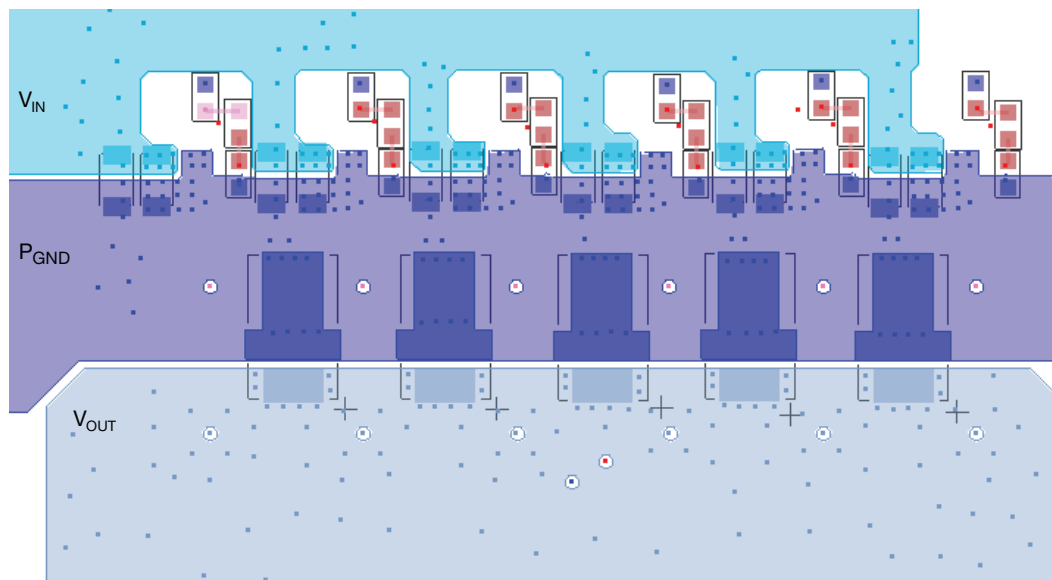


Fig. 29 - Multi - Phase VRPower Layout Bottom View



PRODUCT SUMMARY	
Part number	SiC653A
Description	50 A power stage plus, 4.5 V to 24 V _{IN} , 3.3 V PWM
Input voltage min. (V)	4.5
Input voltage max. (V)	24
Current rating (A)	50
Switch frequency max. (kHz)	1500
Enable (yes / no)	Yes
Monitoring features	T _{HDN}
Protection	UVLO
Light load mode	ZCD
Pulse-width modulation (V)	3.3
Package type	PowerPAK MLP55-31L
Package size (W, L, H) (mm)	5.0 x 5.0 x 0.75
Status code	1
Product type	VRPower (DrMOS)
Applications	Computer, networking

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